

**NTE2366**  
**Silicon PNP Transistor**  
**High Voltage Video Amp**  
**(Compl to NTE399)**

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	300V
Collector–Emitter Voltage, $V_{CEO}$ .....	300V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$	
Continuous .....	100mA
Peak .....	200mA
Power Dissipation, $P_C$ .....	1.0W
Operating Junction Temperature, $T_j$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200V, I_E = 0$	–	–	0.1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$	–	–	0.1	$\mu\text{A}$
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	300	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	300	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5	–	–	V
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 10\text{mA}$	40	–	320	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	–	–	0.6	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	–	–	1.0	V
Current Gain–Bandwidth Product	$f_T$	$V_{CE} = 30V, I_C = 10\text{mA}$	–	150	–	MHz
Capacitance	$C_{ob}$	$V_{CB} = 30V, f = 1\text{MHz}$	–	2.6	–	pF
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = 30V, f = 1\text{MHz}$	–	1.8	–	pF

